

layer and which is made up of multiple semiconductor layers including a first active layer with a composition different from that of the etching control layer; and

a second semiconductor laser structure, which is defined on a second region of the substrate and which is made up of multiple semiconductor layers including a second active layer,

wherein no part of the etching control layer exists between the second region of the substrate and the second semiconductor laser structure.

Please add new claim 18 as follows:

-- 18. (New) A semiconductor laser device comprising:

a buffer layer formed on a compound semiconductor substrate;

an etching control layer formed on the buffer layer and has a composition different from a composition of the substrate;

a first semiconductor laser structure, which is defined in a first region on the etching control layer and which is made up of multiple semiconductor layers including a first active layer with a composition different from that of the etching control layer; and

a second semiconductor laser structure, which is defined in a second region on the etching control layer and which is made up of multiple semiconductor layers including a second active layer. --